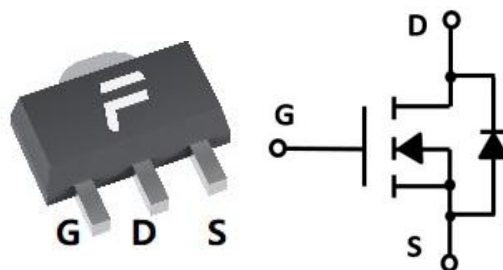


**SOT-89-3L 20V N Channel Enhancement 沟道增强型
MOS Field Effect Transistor 场效应管**



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 12	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	15	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	50	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	3000	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	42	$^\circ C/W$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ **Device Marking 产品字标**

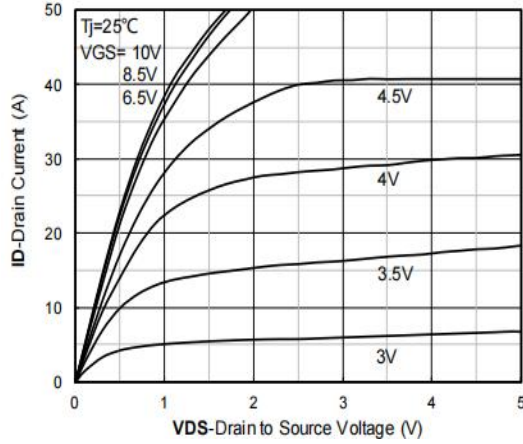
FS15N02F=15N02

■ Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

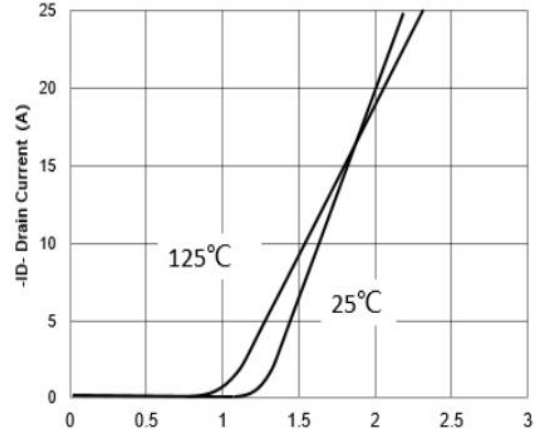
Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D = 250uA, V _{GS} =0V)	BV _{DSS}	20	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	0.4	0.7	1.0	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} = 20V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V _{GS} =±12V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =12A, V _{GS} = 4.5V) (I _D = 7A, V _{GS} = 2.5V)	R _{DS(ON)}	—	6 7	8 9	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} = 12A, V _{GS} =0V)	V _{SD}	—	—	1.2	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{ISS}	—	1650	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{OSS}	—	266	—	pF
Reverse Transfer Capacitance 反馈电容 (V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{RSS}	—	206	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} = 10V, I _D = 4A, V _{GS} = 4.5V)	Q _g	—	50	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} = 10V, I _D = 4A, V _{GS} = 4.5V)	Q _{gs}	—	5	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} = 10V, I _D = 4A, V _{GS} = 4.5V)	Q _{gd}	—	8	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} = 10V I _D = 4A, R _{GEN} =3 Ω, V _{GS} = 4.5V)	t _{d(on)}	—	13	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} = 10V I _D = 4A, R _{GEN} =3 Ω, V _{GS} = 4.5V)	t _r	—	110	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} = 10V I _D = 4A, R _{GEN} =3 Ω, V _{GS} = 4.5V)	t _{d(off)}	—	40	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} = 10V I _D = 4A, R _{GEN} =3 Ω, V _{GS} = 4.5V)	t _f	—	105	—	ns

■ Typical Characteristic Curve 典型特性曲线



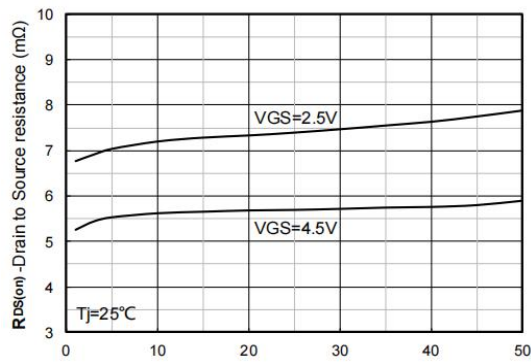
VDS Drain-Source Voltage (V)

Figure 1: Output Characteristics



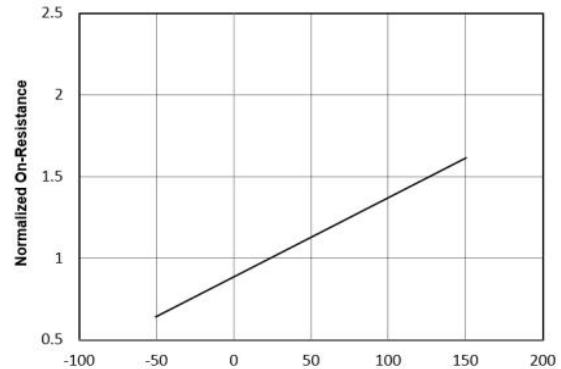
VGS Gate-Source Voltage (V)

Figure 2: Transfer Characteristics



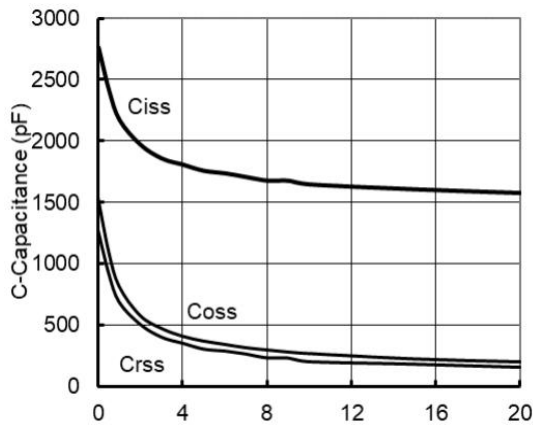
ID Drain Current (A)

Figure 3: On-Resistance vs. Drain Current



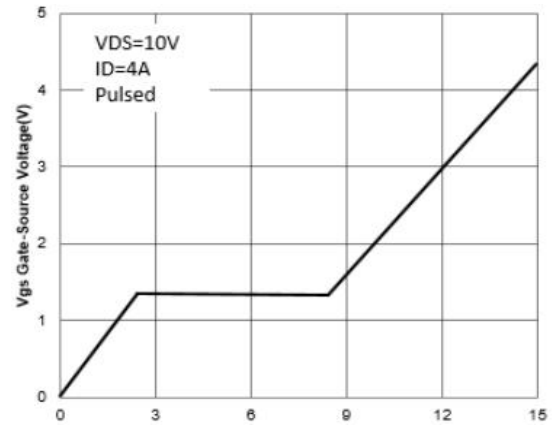
TJ Junction Temperature (°C)

Figure 4: On-Resistance vs. Temperature



VDS Drain-Source Voltage (V)

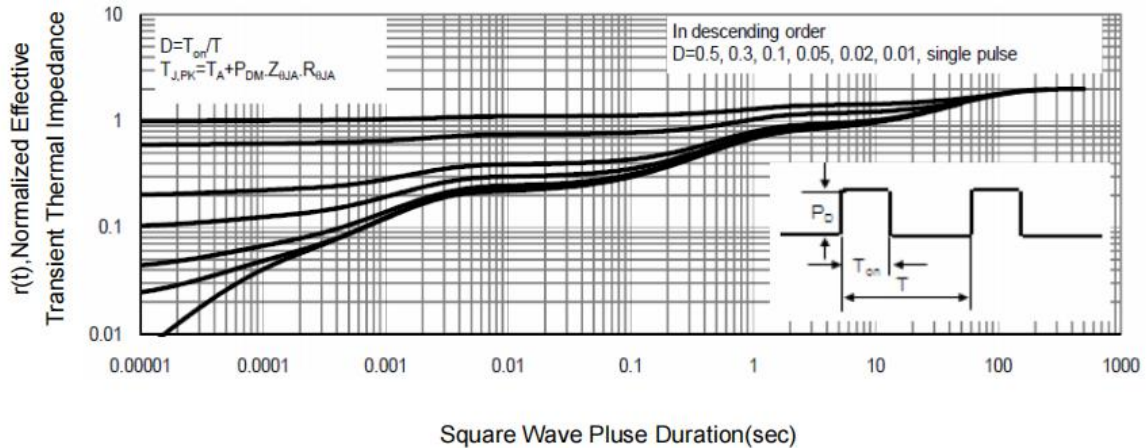
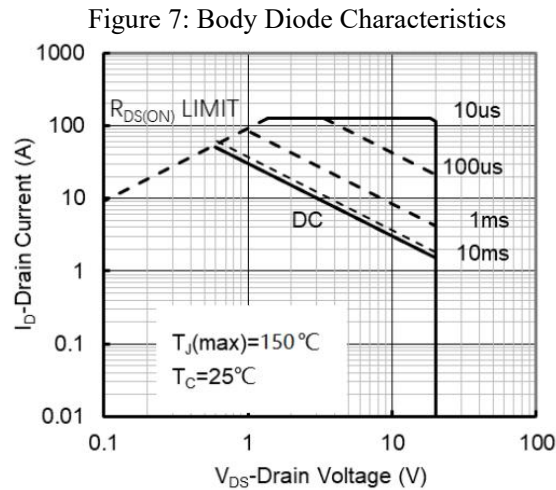
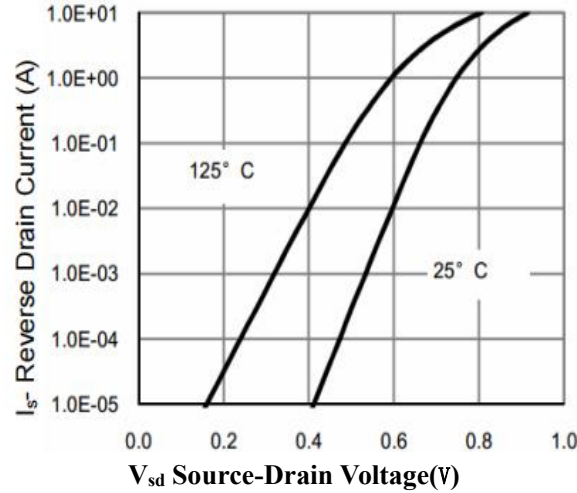
Figure 5: Capacitance Characteristics



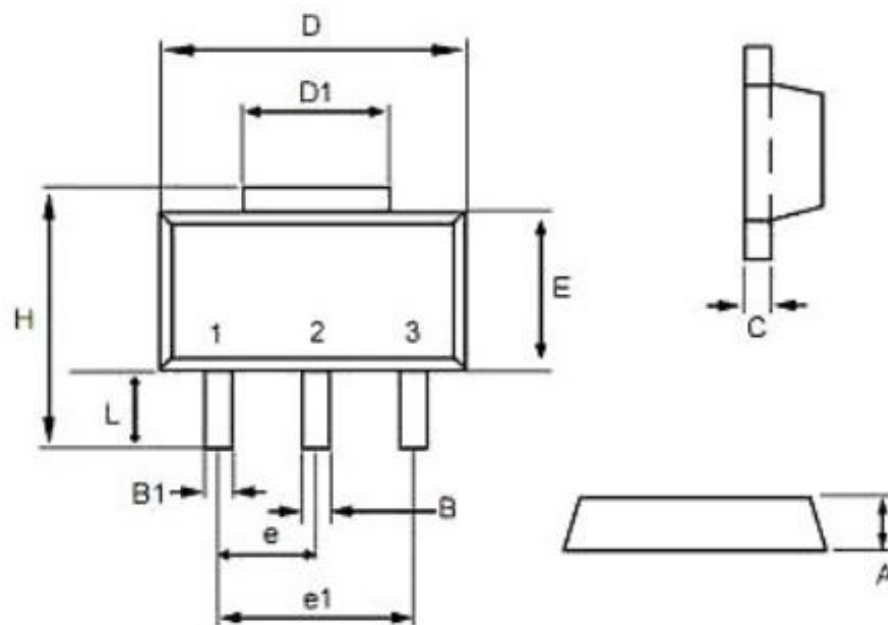
Qg Gate Charge (nC)

Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047